

Features

- Low power consumption
- General purpose leads
- Bulk, Available on tape and reel
- Fast response time
- High photo sensitivity
- Small junction capacitance
- Compliance with EU REACH
- The product itself remain within RoHS compliant version

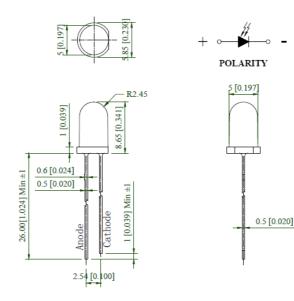
Applications

- High speed photo detector
- Automatic door sensor
- Security system
- Industrial equipment
- Infrared application system

Description

- The INL-5ANPD80 is a high speed and high sensitive silicon PIN photodiode in a standard 5mm epoxy package.
- Due to its black epoxy, the device is sensitive to near and infrared radiation.

Package Dimensions in mm



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is \pm 0.25 mm (.010 $^{\prime\prime}$) unless otherwise noted.

Figure 1. INL-5ANPD80 Package Dimensions



Absolute Maximum Rating at 25°C

| Symbol | Parameters | Ratings | Units | Notes |
|--------|-------------------------|---------|-------|-------|
| VR | Reverse Voltage | 32 | V | 1 |
| Topr | Operating Temperature | -40~+80 | °C | |
| Tstg | Storage Temperature | -40~+85 | °C | |
| Tsol | Soldering Temperature | 260 | °C | 2 |
| PD | Total Power Dissipation | 150 | mW | |

Notes

- 1. Test conditions : IR=100µA, Ee=0mW/cm₂.
- 2. Soldering time \leq 5 seconds.

Electro-Optical Characteristics

| Symbol | Parameters | Test conditions | Min | Тур | Мах | Units |
|---------------|-----------------------------------|---|-----|-----|------|-------|
| λD | Rang of Spectral Bandwidth | | 400 | - | 1100 | nm |
| λP | Wavelength of Peak Sensitivity | | - | 850 | | nm |
| Vbr | Reverse Breakdown Voltage | Ee=0mW/cm2 IR=100uA | 32 | 170 | - | V |
| Voc | Open-Circuit Voltage | Ee=1mW/cm ² λ _P =850nm | - | 0.4 | - | V |
| lsc | Short-Circuit Current | Ee=1mW/cm ² λ _P =850nm | - | 35 | - | uA |
| lo | Dark Current | Ee=0mW/cm ² VR=10V | - | 5 | 30 | nA |
| ١L | Reverse Light Current | Ee=1mW/cm ² λ _P =850nm, VR=5V | 20 | 35 | - | uA |
| tr | Rise Time | VR=10V, | - | 45 | - | uS |
| tr | Fall Time | RL=100Ω | - | 45 | - | uS |
| Ст | Transition Capacitance | Ee=0mW/cm ² f=1MHz, VR=5V | | 18 | | pF |
| 20 1/2 | Receiving Angle | IF=20mA | | 80 | | Deg. |

ESD Precaution

ATTENTION: Electrostatic Discharge (ESD) protection



The symbol above denotes that ESD precaution is needed. ESD protection for GaP and AIGaAs based chips is necessary even though they are relatively safe in the presence of low static-electric discharge. Parts built with AllnGaP, GaN, or/and InGaN based chips are STATIC SENSITIVE devices. ESD precaution must be taken during design and assembly.

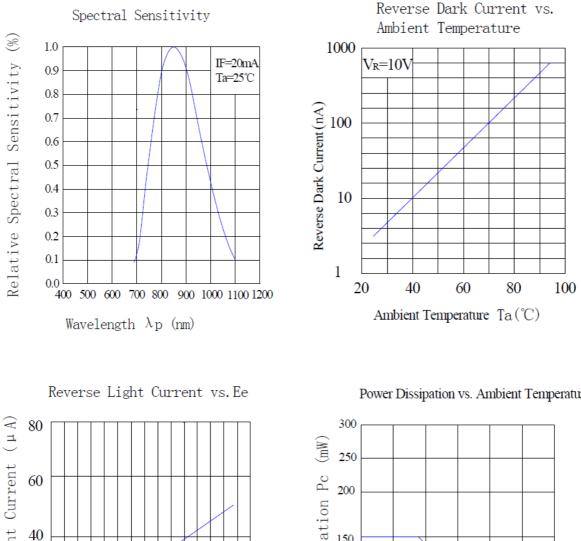
If manual work or processing is needed, please ensure the device is adequately protected from ESD during the process.

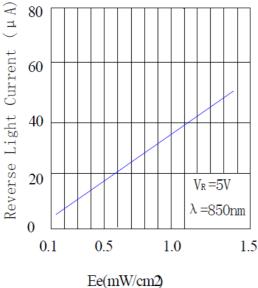
Please be advised that normal static precautions should be taken in the handling and assembly of this device to prevent damage or degradation which may be induced by electrostatic discharge (ESD).



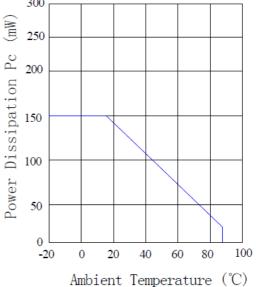
INL-5ANPD80 5mm Photodiode Though Hole Lamp LED

Typical Characteristic Curves

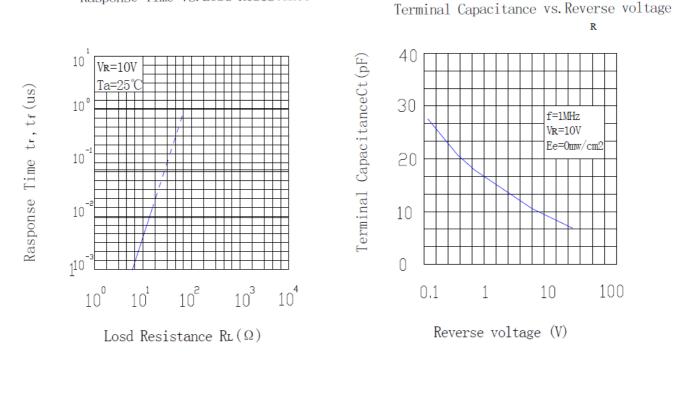




Power Dissipation vs. Ambient Temperature

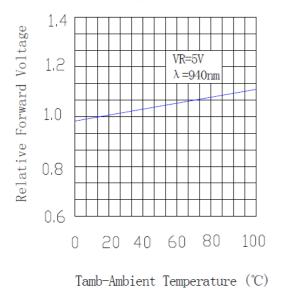




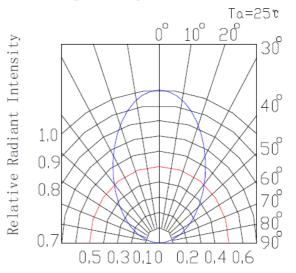


Rasponse Time vs. Losd Resistance

Relative Reverse Light Current vs. Ambient Temperatyre(°C)



Relative Radiant Intensity vs. Angular Displacement

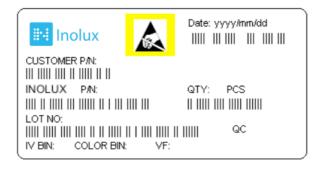




Ordering Information

| Product | Symbol | Parameters | Test conditions | Min | Тур | Max | Units | Orderable Part Number |
|-------------|--------|-----------------------|-------------------------------|-----|-----|-----|-------|--------------------------|
| INL-5ANPD80 | L | Reverse Light Current | Ee=1mW/cm² λ⊧=850nm, VR=5V | 20 | 35 | - | uA | INL-5ANPD80 |

Label Specifications



Inolux P/N:

| I | Ν | L | - | 5 | А | N | PD | 8 | 0 | • | х | х | х | х |
|---|--------------------|---|---|------|-------------------|-----------------------|---------------------|---------|--------|---|---|---|-----------------|---|
| | | | | Pacl | kage | Lens | Color | View A | Angle | | | | mized ıp-off | |
| | Inolux Lamp Typ | e | | stan | A = dard nm | N = Black Epoxy | PD = Photo Diode | 80 = 80 |) deg. | | | | | |

Lot No.:

| Z | 2 | 0 | 1 | 7 | 01 | 24 | 001 |
|----------|---|-------------|----------|-------|------|--------|-----|
| Internal | | Year (2017 | 2019 \ | Month | Data | Serial | |
| Tracker | | fear (2017) | , 2018,) | Month | Date | Serial | |



Reliability

| Item | Frequency/ lots/ samples/ failures | Standards Reference | Conditions |
|------------------------------------|---|------------------------|--|
| | For all reliability | J-STD-020 | 1.) Baking at 85°C for 24hrs |
| Precondition | monitoring tests according to JEDEC Level 2 | | 2.) Moisture storage at 85°C/ 60% R.H. for 168hrs |
| | 1Q/ 1/ 22/ 0 | JESD22-B102-B | Accelerated aging 155°C/ 24hrs |
| Solderability | | And CNS-5068 | Tinning speed: 2.5+0.5cm/s Tinning: A: 215°C/ 3+1s or B: 260°C/ 10+1s |
| | | CNS-5067 | Dipping soldering terminal only |
| Resistance to | | | Soldering bath temperature |
| soldering heat | | | A: 260+/-5°C; 10+/-1s |
| | | 010 44000 | B: 350+/-10°C; 3+/-0.5s |
| | 1Q/ 1/ 40/ 0 | CNS-11829 | 1.) Precondition: 85°C baking for 24hrs |
| Operating life test | | | 85°C/ 60%R.H. for 168hrs |
| | 1Q/ 1/ 45/ 0 | JESD-A101-B | 2.) Tamb25°C; IF=20mA; duration 1000hrs |
| High humidity, high temperature | TQ/ 1/ 45/ 0 | JESD-ATUT-D | Tamb: 85°C Humidity: 85% R.H., IF=5mA |
| bias | | | Duration: 1000hrs |
| | 1Q/ 1/ 20 | IN specs. | Tamb: 55°C |
| High temperature | | | IF=20mA |
| bias | | | Duration: 1000hrs |
| | 1Q/ 1/ 40/ 0 | | Tamb25°C, If=20mA,, Ip=100mA, Duty |
| Pulse life test | | | cycle=0.125 (tp=125 μ s,T=1sec) |
| | | | Duration 500hrs) |
| | 1Q/ 1/ 76/ 0 | JESD-A104-A | A cycle: -40 degree C 15min; +85 degree C |
| Temperature | | IEC 68-2-14, Nb | 15min |
| cycle | | | Thermal steady within 5 min |
| Cycle | | | 300 cycles |
| | | | 2 chamber/ Air-to-air type |
| High humidity | 1Q/ 1/ 40/ 0 | CNS-6117 | 60+3°C |
| storage test | | | 90+5/-10% R.H. for 500hrs |
| High temperature storage test | 1Q/ 1/ 40/ 0 | CNS-554 | 100+10°C for 500hrs |
| Low temperature storage test | 1Q/ 1/ 40/ 0 | CNS-6118 | -40+5°C for 500hrs |



Revision History

| Changes since last revision | Page | Version No. | Revision Date |
|-----------------------------|------|-------------|---------------|
| Initial Release | | 1.0 | 01-24-2019 |
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